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(54) **MEMORY CONFIGURATION OF A COMPOSITE MEMORY DEVICE**

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(57) **ABSTRACT**

The present invention is related to a composite flash memory device comprises a plural sector flash memory array which is divided to plural sector that is a minimum erasing unit of the flash memory device, a flash memory array storing control commands which control a total system of the composite flash memory device and/or the only composite flash memory device in and sharing I/O line of the plural sector flash memory array, the read operation of the flash memory array is enable when the plural sector flash memory array is gained access.

34 Claims, 6 Drawing Sheets